

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|---|------|-----|------|------------------------------|--|----------------------|
| 1 | BRS | L1 | 9 | sato near atsuhiro.in. | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/1 1 18:19 |
| 2 | BRS | L2 | 145 | yamashita near hiroki.in. | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/1 1 18:20 |
| 3 | BRS | L3 | 475 | ozawa near yoshio.in. | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/1 1 18:49 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|---|------|-----|------|---|--|----------------------|
| 4 | BRS | L4 | 307 | 438/294.ccls. | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/1 1 18:52 |
| 5 | BRS | L6 | 4 | (inter-electrode near dielectric) near15 (isolat\$3) | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/1 1 18:54 |
| 6 | BRS | L7 | 4 | (inter near electrode near dielectric) near15 (isolat\$3) | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/1 1 18:54 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|---|------|-----|------|---|--|------------------|
| 7 | BRS | L5 | 155 | (inter-electrode near dielectric) | US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/11 19:00 |
| 8 | BRS | L8 | 4283 | (silicon near oxide or sio) near15 (dielectric near constant) | US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/11 19:01 |
| 9 | BRS | L10 | 2 | ((silicon near oxide or sio) near15 (dielectric near constant)) near15 (inter-electrode\$1) | US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/11 19:02 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|---|--|----------------------|
| 10 | BRS | L11 | 2 | ((silicon near oxide or sio) near15 (dielectric near constant)) near15 (inter near electrode\$1) | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/1 1 19:02 |
| 11 | BRS | L9 | 247 | ((silicon near oxide or sio) near15 (dielectric near constant)) near15 (electrode\$1) | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/1 1 19:15 |
| 12 | BRS | L12 | 59 | ((silicon near oxide or sio) near15 (dielectric near constant)) near15 (ono) | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/1 1 19:06 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|---|--|------------------|
| 13 | BRS | L13 | 38 | ((silicon near oxide or sio) near15 (dielectric near constant)) near15 (memory near cell) | US-PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/11 19:06 |
| 14 | BRS | L14 | 94 | ((silicon near oxide or sio) near15 (dielectric near constant)) near15 (conducti\$3) | US-PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/11 19:27 |
| 15 | BRS | L15 | 2 | ((silicon near oxide or sio) near15 (dielectric near constant)) near15 (row or column) | US-PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2005/01/11 19:28 |

| | U | 1 | Document ID | Title | Current OR |
|---|---|---|-------------------------|--|------------|
| 1 | X | | US 20050003619 A1 | Nonvolatile semiconductor memory and manufacturing method for the same | 438/294 |
| 2 | X | | US 20050002231 A1 | Nonvolatile semiconductor memory and manufacturing method for the same | 365/185.01 |
| 3 | X | | US 20020094622 A1 | Process flow for a performance enhanced MOSFET with self- aligned, recessed channel | 438/197 |
| 4 | X | | US 5792689 A | Double crown capacitor formation for use in DRAM - gives self alignment to node contacts and uses single photoresist masking step | |